

LED CHIP CN850-40S

SPECIFICATION OF LED CHIP CN850-40S [INFRARED]

1) Commodity Type and Physical Characteristics.

- | | | |
|----------------------|---------------------|-----------------------------|
| 1. Material | GaAlAs/GaAlAs (DDH) | |
| 2. Electrode | Top Side | P (anode) side : Au Alloy |
| | Bottom Side | N (cathode) side : Au Alloy |
| 3. Electrode Pattern | Fig.1 | |
| 4. Chip Size | Fig.2 | |
| 5. Chip Thickness | Fig.2 | |
| 6. Emission Area | Fig.2 | |

2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.35	1.6	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	2.0	4.0		mW
Peak Wavelength	λ P	If=20mA	840	850	860	nm
Spectral Radiation Bandwidth	Δλ	If=20mA		35		nm
RiseTime	tr	If=20mA		15		ns
FallTime	tf	If=20mA		10		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.(Ta=25°C)

[Unit : um]

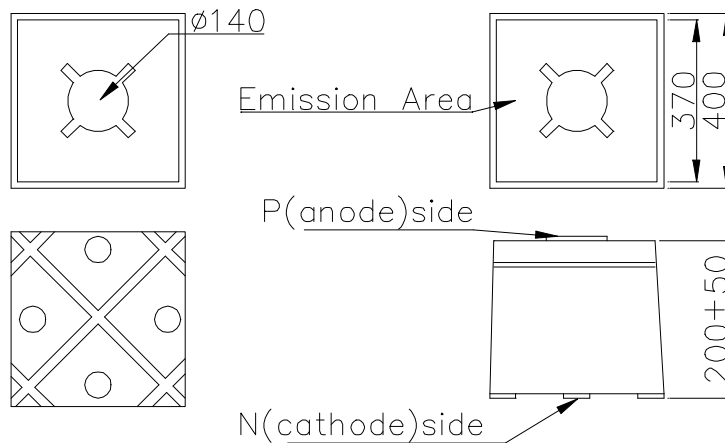


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area